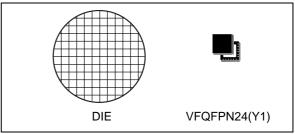
ST7LCRE4U1 ST7LCRDIE6

Full-speed USB MCU with smartcard interface

Features

- Clock, reset and supply management
 - Low voltage reset
 - Halt power saving mode
 - PLL for generating 48 MHz USB clock using a 4 MHz crystal
- USB (Universal Serial Bus) host interface
 - USB 2.0 compliant
 - CCID v1.0
 - Full speed, hubless
 - Bus-powered, low consumption
- ISO7816-3 UART Interface
 - 4 MHz clock generation
 - Synchronous/asynchronous protocols (T=0, T=1)
 - Automatic retry on parity error
 - Programmable baud rate from 372 to 11.625 clock pulses (D=32/F=372)
 - Card insertion/removal detection
- Smartcard power supply
 - Fixed card V_{CC}: 1.8 V, and 3 V
 - Internal step-up converter for 5 V supplied smartcards (with current of up to 55 mA) using only two external components



- Programmable smartcard internal voltage regulator (1.8 to 3.0V) with current overload protection and 4 kV ESD protection (human body model) for all smartcard Interface I/Os
- Development tools
 - Full hardware/software development package.
 - Fully compatible with Flash ST7FSCR family for development purposes
- ECOPACK[®] package

Description

ST7LCRE4U1 and ST7LCRDIE6 are an 8-bit microcontrollers dedicated to smartcard reading applications. They have been developed to be the core of smartcard readers communicating through USB link. Optimized for mass-market applications, it offers a single integrated circuit solution with very few external components.

Table 1. Device summary

Factoria	Part n	umbers			
Features —	ST7LCRE4U1	ST7LCRDIE6			
Program memory	16 Kbyt	e of ROM			
User RAM + USB data buffer	512 + 2	256 bytes			
Peripherals	USB full-speed (7 Ep), TBU, wa	tchdog timer, ISO7816-3 interface			
Operating Supply	4.0 t	o 5.5 V			
Package	VFQFPN24	Die format (Refer to Die Specifications)			
CPU Frequency	4 or	8 MHz			
Operating temperature	0°C to +70 °C				

Contents

1	Des	cription		5
2	Pin	descript	ion	7
3	ST7	LCR imp	olementation	10
	3.1	Function	onality	10
	3.2	Smarto	card interface features	10
4	Elec	trical ch	naracteristics	11
	4.1	Absolu	ite maximum ratings	11
	4.2	Recom	nmended operating conditions	12
		4.2.1	General operating conditions	
		4.2.2	Current injection	12
		4.2.3	Current consumption	13
		4.2.4	I/O port pin characteristics	13
	4.3	Supply	and reset characteristics	14
	4.4	Clock a	and timing characteristics	14
		4.4.1	General timings	14
		4.4.2	External clock source	15
		4.4.3	Crystal resonator oscillators	16
	4.5	Memor	ry characteristics	17
	4.6	Smarto	card supply supervisor electrical characteristics	17
	4.7	EMC c	characteristics	19
		4.7.1	Functional EMS (electromagnetic susceptibility)	19
		4.7.2	Electromagnetic interference (EMI)	20
		4.7.3	Absolute maximum ratings (electrical sensitivity)	20
	4.8	Comm	unication interface characteristics	21
5	Pack	kage cha	aracteristics	23
	5.1	Packaç	ge mechanical data	24
6	Devi	ce conf	iguration and ordering information	26
7	Revi	sion his	story	28

List of tables

rable 1.	Device summary	1
Table 2.	Pin description	7
Table 3.	Absolute maximum ratings	. 11
Table 4.	Thermal characteristics	. 12
Table 5.	General operating conditions	. 12
Table 6.	Current injection on I/O port and control pins	. 13
Table 7.	Current consumption	. 13
Table 8.	I/O port pins characteristics	. 13
Table 9.	Low voltage detector and supervisor (LVDs)	. 14
Table 10.	General timings	. 14
Table 11.	External clock source characteristics	. 15
Table 12.	Crystal resonator characteristics	. 16
Table 13.	Typical crystal resonator characteristics	
Table 14.	Recommended values for 4 MHz crystal resonator	. 16
Table 15.	RAM and hardware registers characteristics	. 17
Table 16.	Smartcard supply supervisor electrical characteristics	. 17
Table 17.	EMS characteristics	. 19
Table 18.	EMI characteristics	. 20
Table 19.	Absolute maximum ratings	. 20
Table 20.	Electrical sensitivities	. 21
Table 21.	USB DC electrical characteristics	. 21
Table 22.	USB full-speed electrical characteristics	
Table 23.	24-lead very thin fine pitch quad flat no-lead 5x5mm,0.65mm pitch, mechanical data	. 24
Table 24.	Ordering information	. 26
Table 25.	Document revision history	. 28

List of figures

Figure 1.	ST7LCR block diagram	6
Figure 2.	24-lead VFQFPN package pinout	
Figure 3.	Smartcard interface reference application - VFQFPN24 pin block diagram	
Figure 4.	Typical application with an external clock source	
Figure 5.	Typical application with a crystal resonator	17
Figure 6.	USB data signal rise and fall time	
Figure 7.	24-lead very thin fine pitch quad flat no-lead 5x5 mm 0.65 mm pitch, package outline	
Figure 8.	Recommended reflow oven profile (MID JEDEC)	
Figure 9.	ST7LCR option list	

1 Description

The ST7LCRE4U1 and ST7LCRDIE6 devices are members of the ST7 microcontroller family designed for USB applications. All devices are based on a common industry-standard 8-bit core, featuring an enhanced instruction set.

ST7LCRE4U1 and ST7LCRDIE6 are factory-programmed ROM devices.

They operate at a 4 MHz external oscillator frequency.

Under software control, all devices can be placed in Halt mode, to reduce power consumption when the application is in idle or standby state.

The enhanced instruction set and addressing modes of the ST7 offer both power and flexibility to software developers, enabling the design of highly efficient and compact application code. In addition to standard 8-bit data management, all ST7 microcontrollers feature true bit manipulation, 8x8 unsigned multiplication and indirect addressing modes.

The devices include an ST7 Core, up to 16 Kbytes of program memory, up to 512 bytes of user RAM and the following on-chip peripherals:

- USB full speed interface with 7 endpoints, programmable in/out configuration and embedded 3.3 V voltage regulator and transceivers (no external components are needed)
- ISO7816-3 UART interface with programmable baud rate from 372 clock pulses up to 11.625 clock pulses
- Smartcard supply block able to provide programmable supply voltage and I/O voltage levels to the smartcards
- Low voltage reset ensuring proper power-on or power-off of the device (selectable by option)
- 8-bit Timer (TBU)

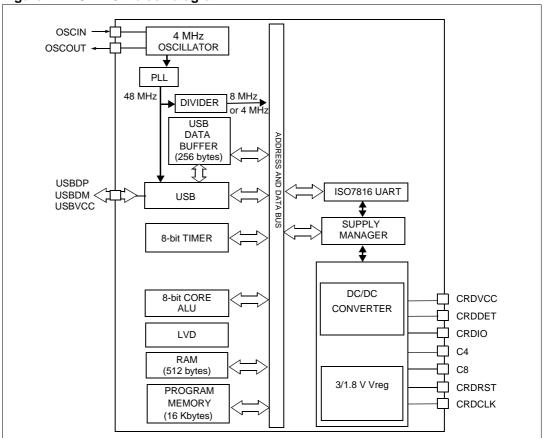


Figure 1. ST7LCR block diagram

2 Pin description



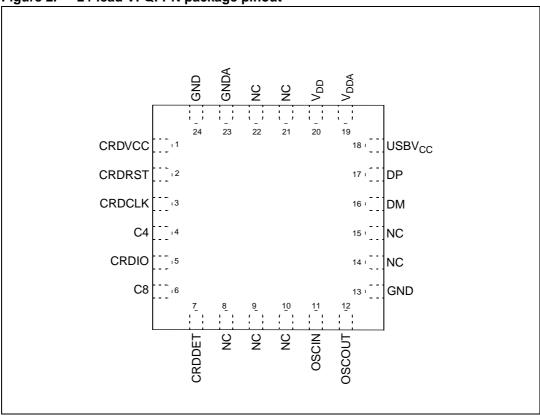


Table 2. Pin description

145.0 2.	i iii doconption											
Pin			Le	vel	lied	P	ort/c	onti	ol			
number	Pin name	Туре	<u>+</u>	rt	supplied		Input Out		put		Alternate function	
VFQFPN24		Ţ	Input	Output	VCARD	ndw	int	QO	ЬР	(after reset)		
1	CDRVCC	0		C_{T}	Χ					Sma	rtcard supply pin	
2	CRDRST	0		СТ	Χ				Х	Smartcard reset		
3	CRDCLK	0		СТ	Χ				Х	Sr	martcard clock	
4	C4	0		C_{T}	Χ				Х	S	Smartcard C4	
5	CRDIO	I/O	C	C _T	Χ	Χ		Х		S	Smartcard I/O	
6	C8	0		C _T	Х				Х	S	Smartcard C8	
7	CRDDET	I	C _T			Χ				Sma	artcard detection	
8	NC									Not used ⁽¹⁾		
9	NC									Not used ⁽¹⁾		
10	NC										Not used ⁽¹⁾	

Table 2. Pin description (continued)

	i iii acsoriptioni	`		,							
Pin			Le	vel	olied	Po	ort/c	onti	ol		
number	Pin name	Type	ıt	ut	supplied	Inp	ut	Out	put	Main function (after reset)	Alternate function
VFQFPN24		F.	Input	Output	VCARD	wpu	int	ОО	PP	(arter reset)	
11	OSCIN		C_{T}							•	oscillator pins. These pins
12	OSCOUT			C_T							parallel-resonant crystal, or rce to the on-chip oscillator.
13	GND	S								Must be held lov	w in normal operating mode.
14	NC									Not used ⁽¹⁾	
15	NC									Not used	
16	DM	I/O	C	, T						USB	Data Minus line
17	DP	I/O	C	, T						USI	3 Data Plus line
18	USBVCC	0		C_{T}						3.3 \	Output for USB
19	V_{DDA}	S								Power su	upply voltage 4-5.5 V
20	V _{DD}	S								Power su	upply voltage 4-5.5 V
21	NC									Not used	
22	NC										Not used
23	GNDA	S								- Ground	
24	GND	S									

^{1.} Pins 8,9,10, and 14 must be connected to ground.

Legend/abbreviations

- Type: I = input, O = output, S = supply
- In/Output level: $C_T = CMOS \ 0.3V_{DD}/0.7V_{DD}$ with input trigger
- Output level: HS = 10 mA high sink (on N-buffer only)
- Port and control configuration:
 - Input: float = floating, wpu = weak pull-up, int = interrupt, ana = analog
 - Output: OD = open drain, PP = push-pull

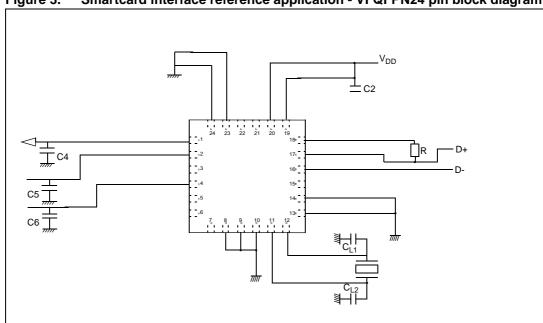


Figure 3. Smartcard interface reference application - VFQFPN24 pin block diagram

1. Mandatory values for the external components: $C1 = 4.7 \, \mu\text{F}, \, C2 = 100 \, \text{nF}. \, C1 \, \text{and} \, C2 \, \text{must} \, \text{be} \, \text{located} \, \text{close} \, \text{to} \, \text{the} \, \text{chip.}$ $C3 = 1 \, \text{nF}$ $C4 = 4.7 \, \mu\text{F}, \, \text{ESR} = 0.5\Omega$ $C5 = 470 \, \text{pF}$ $C6 = 100 \, \text{pF}$ $R = 1.5 \, \text{k}\Omega$ $L1 = 10 \, \mu\text{H}, \, 2\, \Omega$ $\text{Crystal} \, 4.0 \, \text{MHz}, \, \text{maximum} \, \text{impedance} = 100 \, \Omega$ $\text{Cl1,} \, \text{Cl2} \, (\text{refer} \, \text{Section} \, 4.4.3: \, \text{Crystal resonator} \, \text{oscillators}).$ $\text{D1:} \, \text{BAT42 Shottky}$

3 ST7LCR implementation

ST7LCRE4U1 and ST7LCRDIE6 offer single IC solutions and simplifies the integration of smartcard interfaces into smartcard readers.

3.1 Functionality

A dedicated analog block provides the power supplies 1.8 V and 3 V necessary to interface with different smartcard voltages available on the market. Voltages are selected by software. A dedicated UART interface provides an IS07816 communication port for connection with the smartcard connector. A full-speed USB interface port allows external connection to a host computer.

3.2 Smartcard interface features

The ST7LCRE4U1 and ST7LCRDIE6 include the following features:

- Compatibility with asynchronous cards
- Compatibility with T=0 and T=1 protocols
- Compatibility with EMV and PC/SC modes.
- Compliance with ISO 7816-3 and 4 and ability to supply the cards with 1.8 V or 3 V (class A, B or C cards, respectively)
- Resume/wake-up mode upon smartcard insertion/removal

The reader is able to communicate with smartcards up to the maximum baud rate allowed, namely 344 086 bps (TA1=16) for a clock frequency of 4 MHz. Because the size of the smartcard buffer is 261 bytes, care must be taken not to exceed this size during APDU exchanges when the protocol in use is T=1.

4 Electrical characteristics

4.1 Absolute maximum ratings

This product contains devices for protecting the inputs against damage due to high static voltages, however it is advisable to take normal precautions to avoid applying any voltage higher than the specified maximum rated voltages. For proper operation it is recommended that V_I and V_O be higher than V_{SS} and lower than V_{DD} . Reliability is enhanced if unused inputs are connected to an appropriate logic voltage level (V_{DD} or V_{SS}).

Power considerations

The average chip-junction temperature, T_{.I}, in Celsius can be obtained from:

$$T_{I} = T_{\Delta} + PD \times RthJA$$

where:

 T_{Δ} = Ambient temperature

RthJA = Package thermal resistance (junction-to ambient)

 $P_D = P_{INT} + P_{PORT}$

 $P_{INT} = I_{DD} \times V_{DD}$ (chip internal power)

P_{PORT} = Port power dissipation determined by the user

Stresses above those listed as "absolute maximum ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions is not implied. Exposure to maximum rating for extended periods may affect device reliability.

Table 3. Absolute maximum ratings

Symbol	Ratings	Value	Unit
V _{DD} - V _{SS}	Supply voltage	6.0	V
V _{IN}	Input voltage	V _{SS} - 0.3 to V _{DD} + 0.3	V
V _{OUT}	Output voltage	V_{SS} - 0.3 to V_{DD} + 0.3	V
ESD	ESD susceptibility	2000	V
ESDCard	ESD susceptibility for card pads	4000	V
I _{VDD_I}	Total current into V _{DD_I} (source)	250	mA
I _{VSS_I}	Total current out of V _{SS_I} (sink)	250	IIIA

Warning:

Direct connection to V_{DD} or V_{SS} of the I/O pins could damage the device in case of program counter corruption (due to unwanted change of the I/O configuration). To guarantee safe conditions, this connection has to be done through a typical $10k\Omega$ pull-up or pull-down resistor.

Table 4. Thermal characteristics

Symbol	Ratings	Value	Unit
R _{thJA}	Package thermal resistance VFQFPN24	42	°C/W
T _{Jmax}	Max. junction temperature	150	°C
T _{STG}	Storage temperature range	-65 to +150	°C
PD _{max}	Power dissipation VFQFPN24	600	mW

4.2 Recommended operating conditions

Operating conditions are given for $T_A = 0$ to +70 °C unless otherwise specified.

4.2.1 General operating conditions

Table 5. General operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DD}	Supply voltage		4.0		5.5	V
f _{OSC}	External clock source				16	MHz
T _A	Ambient temperature range		0		70	°C

4.2.2 Current injection

Positive injection

The positive injection current, I_{INJ+}, is **applied** through protection diodes insulated from the substrate of the die.

Negative injection

The negative injection current, I_{INJ} , is **applied** through protection diodes NOT INSULATED from the substrate of the die. The drawback is a small leakage of few μA induced inside the die when a negative injection is performed. This leakage is tolerated by the digital structure. The effect depends on the pin which is submitted to the injection. Of course, external digital signals applied to the component must have a maximum impedance close to 50 k Ω .

Pure digital pins can tolerate a negative current injection of 1.6 mA. In addition, the best choice is to inject the current as far as possible from the analog input pins.

Note:

When several inputs are submitted to a current injection, the maximum injection current is the sum of the positive (respectively negative) currents (instantaneous values).

Refer to Table 6 for the values of I_{INJ-} and I_{INJ+} .

Table 6. Current injection on I/O port and control pins

Symbol	Parameter	Conditions			Тур	Max	Unit
	Total positive injected	V _{EXTERNAL} > V _{DD} (standard I/Os)				20	mA
I _{INJ+}	current ⁽¹⁾	V _{EXTERNAL} > V _{CRDV} I/Os)			20	mA	
	Total negative	V ~V.	Digital pins			20	mA
INJ-	injected current	V _{EXTERNAL} < V _{SS} Analog pins				20	mA

^{1.} For SmartCard I/Os, V_{CRDVCC} has to be considered.

4.2.3 Current consumption

Table 7 are measured at TA=0 to +70°C, and VDD-VSS=5.5 V unless otherwise specified.

Table 7. Current consumption⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	Supply current in Run mode ⁽²⁾	$f_{OSC} = 4 \text{ MHz}$		10	15	mA
I _{DD}	Supply current in suspend mode	External I _{LOAD} = 0 mA (USB transceiver enabled)			500	μΑ
	Supply current in Halt mode	External I _{LOAD} = 0 mA (USB transceiver disabled)		50	100	μΑ

All I/O pins are in input mode with a static value at V_{DD} or V_{SS}. Clock input (OSCIN) is driven by external square wave.

4.2.4 I/O port pin characteristics

Table 8 characteristics are measured at TA=0 to +70 $^{\circ}$ C. Voltages are referred to V_{SS} unless otherwise specified.

Table 8. I/O port pins characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL}	Input low level voltage	V _{DD} = 5 V			0.3V _{DD}	V
V_{IH}	Input high level voltage	V _{DD} = 5 V	$0.7V_{DD}$			V
V _{HYS}	Schmidt trigger voltage hysteresis ⁽¹⁾			400		mV
V	Output low level voltage for Standard I/O	I=-5mA			1.3	
V _{OL}	port pins	I=-2mA			0.4	V
V _{OH}	Output high level voltage	I=3mA	V _{DD} - 0.8			
ΙL	Input leakage current	$V_{SS} < V_{PIN} < V_{DD}$			1	μΑ
R _{PU}	Pull-up equivalent resistor		50	90	170	kΩ

CPU running with memory access, all I/O pins in input mode with a static value at V_{DD} or V_{SS}; clock input (OSCIN) driven by external square wave.

	are personal (community)								
Symbol	Parameter	Conditions	Min	Тур	Max	Unit			
t _{OHL}	Output high to low level fall time for high sink I/O port pins (Port D) ⁽²⁾	r high		8	13				
t _{OHL}	Output high to low level fall time for standard I/O port pins (Port A, B or C) ⁽²⁾	to low level fall time for ort pins (Port A, B or C) ⁽²⁾ C _I =50 pF			23	ns			
t _{OLH}	Output L-H rise time (Port D) ⁽²⁾		7	9	14				
t _{OLH}	Output L-H rise time for standard I/O port pins (Port A, B or C) ⁽²⁾		19		28				
titext	External interrupt pulse time		1			topu			

Table 8. I/O port pins characteristics (continued)

4.3 Supply and reset characteristics

Table 9 characteristics are measured for $T_A = 0$ to +70 °C, and V_{DD} - $V_{SS} = 5.5$ V unless otherwise specified.

Table 9. Low voltage detector and supervisor (LVDs)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IT+}	Reset release threshold (V _{DD} rising)			3.7	3.9	V
V _{IT-}	Reset generation threshold (V _{DD} falling)		3.3	3.5		V
V _{hys}	Hysteresis V _{IT+} - V _{IT-} ⁽¹⁾			200		mV
V _{tPOR}	V _{DD} rise time rate ⁽¹⁾		20			ms/V

^{1.} Hysteresis voltage between Schmitt trigger switching levels. Based on characterization results, not tested.

4.4 Clock and timing characteristics

4.4.1 General timings

Table 10 are measured at TA=0 to +70 °C unless otherwise specified.

Table 10. General timings

Symbol	Parameter	Conditions	Min	Typ ⁽¹⁾	Max	Unit
t _{c(INST)}	Instruction cycle time		2	3	12	t _{CPU}
	mstruction cycle time	f _{CPU} =4 MHz	500	750	3000	ns
t _{v(IT)}	Interrupt reaction time		10		22	t _{CPU}
	$t_{v(IT)} = \Delta t_{c(INST)} + 10^{(2)}$	f _{CPU} =4 MHz	2.5		5.5	μS

^{1.} Data based on typical application software.

^{1.} Hysteresis voltage between Schmitt trigger switching levels. Based on characterization results, not tested.

^{2.} Guaranteed by design, not tested in production.

^{2.} Time measured between interrupt event and interrupt vector fetch. $\Delta t_{c(INST)}$ is the number of t_{CPU} cycles needed to finish the current instruction execution.

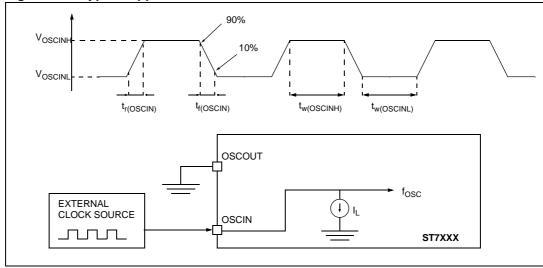
4.4.2 External clock source

Table 11. External clock source characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OSCINH}	OSCIN input pin high level voltage		0.7V _{DD}		V_{DD}	V
V _{OSCINL}	OSCIN input pin low level voltage		V_{SS}		0.3V _{DD}	V
$\begin{array}{c} t_{\text{w(OSCINH)}} \\ t_{\text{w(OSCINL)}} \end{array}$	OSCIN high or low time ⁽¹⁾	see Figure 4	15			ns
$t_{r(OSCIN)} \ t_{f(OSCIN)}$	OSCIN rise or fall time				15	110
IL	OSCx Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$			±1	μА

^{1.} Data based on design simulation and/or technology characteristics, not tested in production.

Figure 4. Typical application with an external clock source



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4.4.3 Crystal resonator oscillators

The ST7 internal clock is supplied with one Crystal resonator oscillator. All the information given in this paragraph are based on characterization results with specified typical external components. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and start-up stabilization time. Refer to the crystal resonator manufacturer for more details (frequency, package, accuracy...).

Table 12. Crystal resonator characteristics

Symbol	Parameter	Conditio	Min	Тур	Max	Unit	
f _{OSC}	Oscillator Frequency ⁽¹⁾	MP: Medium pow		4		MHz	
R _F	Feedback resistor		90		150	kΩ	
C _{L1} C _{L2}	Recommended load capacitances versus equivalent serial resistance of the crystal resonator (R _S)	See Table 14	(MP oscillator)	22		56	pF
i ₂	OSCOUT driving current	V_{DD} =5 V V_{IN} = V_{SS}	(MP oscillator)	1.5		3.5	mA

The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R_S value. Contact crystal resonator manufacturer for more details.

Table 13. Typical crystal resonator characteristics

Oscillato	or	Reference		Freq.	Characteristic ⁽¹⁾	C _{L1} (pF)	C _{L2} (pF)	t _{SU(osc)} (ms) ⁽²⁾
Crystal	MP	JAUCH	SS3-400-30- 30/30	4 MHz	Δf_{OSC} =[±30ppm _{25°C} ,±30ppm _{ΔTa}] (Typ) R_S =60 Ω	33	33	7~10

^{1.} Resonator characteristics given by the crystal resonator manufacturer.

Table 14. Recommended values for 4 MHz crystal resonator

Symbol	Min	Тур	Max
R _{SMAX} ⁽¹⁾	20 Ω	25 Ω	70 Ω
C _{OSCIN}	56 pF	47 pF	22 pF
C _{OSCOUT}	56 pF	47 pF	22 pF

^{1.} R_{SMAX} is the equivalent serial resistor of the crystal (see crystal specification).

^{2.} $t_{SU(OSC)}$ is the typical oscillator start-up time measured between V_{DD} = 2.8 V and the fetch of the first instruction (with a quick V_{DD} ramp-up from 0 to 5 V (<50 μ s).

WHEN RESONATOR WITH INTEGRATED CAPACITORS

OSCIN

RESONATOR

ST7XXX

Figure 5. Typical application with a crystal resonator

4.5 Memory characteristics

Subject to general operating conditions for V_{DD} , f_{OSC} , and T_A unless otherwise specified.

Table 15. RAM and hardware registers characteristics

Symbo	l Parameter	Conditions	Min	Тур	Max	Unit
V_{RM}	Data retention mode ⁽¹⁾	Halt mode (or Reset)	2			V

Minimum V_{DD} supply voltage without losing data stored in RAM (in Halt mode or under Reset) or in hardware registers (only in Halt mode). Not tested in production.

4.6 Smartcard supply supervisor electrical characteristics

Table 16 characteristics are measured for T_A = 0 to +70 °C, and 4.0 < V_{DD} - V_{SS} < 5.5 V unless otherwise specified.

Table 16. Smartcard supply supervisor electrical characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
3 V regulat	or output (for IEC7816-3 class B ca	ards)				
V _{CRDVCC}	SmartCard Power Supply Voltage		2.7	3.0	3.3	V
I _{SC}	SmartCard Supply Current				50	mA
I _{OVDET}	Current Overload Detection				100 ⁽¹⁾	mA
t _{IDET}	Detection time on Current Overload		170 ⁽¹⁾		1400 ⁽¹⁾	μs
t _{OFF}	V _{CRDVCC} Turn off Time	C _{LOADmax} ≤4.7uF			750	μs
t _{ON}	V _{CRDVCC} Turn on Time	$C_{LOADmax} \leq 4.7 uF$		150	500	μs
1.8 V regula	ator output (for IEC7816-3 Class C	Cards)				
V _{CRDVCC}	SmartCard Power Supply Voltage		1.65	1.8	1.95	V
I _{SC}	SmartCard Supply Current				20	mA
I _{OVDET}	Current Overload Detection				100 ⁽¹⁾	mA

Table 16. Smartcard supply supervisor electrical characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{IDET}	Detection time on Current Overload		170 ⁽¹⁾		1400 ⁽¹⁾	μs
t _{OFF}	V _{CRDVCC} Turn off Time	$C_{LOADmax} \le 4.7uF$			750	μs
t _{ON}	V _{CRDVCC} Turn on Time	$C_{LOADmax} \le 4.7uF$		150	500	μs
Smartcard	CLKPin					
V _{OL}	Output Low Level Voltage	I=-50uA	-	-	0.4 ⁽¹⁾	V
V _{OH}	Output High Level Voltage	I=50uA	V _{CRDVCC} - 0.5 ⁽¹⁾	-	-	V
T _{OHL}	Output H-L Fall Time ⁽¹⁾	C _l =30pF	-		20	ns
T _{OLH}	Output L-H Rise Time ⁽¹⁾	C _l =30pF	-		20	ns
F _{VAR}	Frequency variation ⁽¹⁾		-		1	%
F _{DUTY}	Duty cycle ⁽¹⁾		45		55	%
P _{OL}	Signal low perturbation ⁽¹⁾		-0.25		0.4	V
P _{OH}	Signal high perturbation ⁽¹⁾		V _{CRDVCC} -0.5		V _{CRDVCC} +0.2	V
I _{SGND}	Short-circuit to Ground ⁽¹⁾			15		mA
Smartcard	I/O Pin					
V _{IL}	Input Low Level Voltage		-	-	0.5 ⁽¹⁾	V
V _{IH}	Input High Level Voltage		0.6V _{CRDVCC} ⁽¹⁾	-	-	V
V _{OL}	Output Low Level Voltage	I=-0.5mA	-	-	0.4 (1)	V
V _{OH}	Output High Level Voltage	I=20uA	0.8V _{CRDVCC} ⁽¹⁾	-	V _{CRDVCC} ⁽¹⁾	V
IL	Input Leakage Current (1)	V _{SS} <v<sub>IN<v<sub>SC_PWR</v<sub></v<sub>	-10	-	10	μΑ
I _{RPU}	Pull-up Equivalent Resistance	V _{IN} =V _{SS}		24	30	kΩ
T _{OHL}	Output H-L Fall Time ⁽¹⁾	C _l =30pF	-		0.8	μs
T _{OLH}	Output L-H Rise Time ⁽¹⁾	C _l =30pF	-		0.8	μs
I _{SGND}	Short-circuit to Ground ⁽¹⁾			15		mA
Smartcard	RST C4 and C8 Pin					
V _{OL}	Output Low Level Voltage	I=-0.5mA	-	-	0.4 ⁽¹⁾	V
V _{OH}	Output High Level Voltage	I=20uA	V _{CRDVCC} - 0.5 ⁽¹⁾	-	V _{CRDVCC} ⁽¹⁾	V
T _{OHL}	Output H-L Fall Time ⁽¹⁾	C _l =30pF	-		0.8	μs
T _{OLH}	Output L-H Rise Time ⁽¹⁾	C _l =30pF	-		0.8	μs
I _{SGND}	Short-circuit to Ground ⁽¹⁾			15		mA

^{1.} Data based on characterization results, not tested in production.

4.7 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

4.7.1 Functional EMS (electromagnetic susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electromagnetic events until a failure occurs (indicated by the LEDs).

- ESD: electrostatic discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 1000-4-2 standard.
- FTB: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 1000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)
- Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the Reset pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Table 17. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V _{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V _{DD} =5 V, T _A =+25 °C, f _{OSC} =8 MHz conforms to IEC 1000-4-2	2B
V _{FFTB}	Fast transient voltage burst limits to be applied through 100 pF on V _{DD} and V _{DD} pins to induce a functional disturbance	V _{DD} =5 V, T _A =+25 °C, f _{OSC} =8 MHz conforms to IEC 1000-4-4	4B

4.7.2 Electromagnetic interference (EMI)

Based on a simple application running on the product (toggling 2 LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm SAE J 1752/3 which specifies the board and the loading of each pin.

Table 18. EMI characteristics

Symbol	Parameter	Conditions	Monitored Frequency	Max [f _{OSC} /f	Unit	
			Band	4/8MHz	4/4MHz	
		V _{DD} =5 V, T _A =+25 °C, conforming to SAE J 1752/3	0.1 MHz to 30 MHz	19	18	
S _{EMI}	Peak level		30 MHz to 130 MHz	32	27	dΒμV
			130 MHz to 1 GHz	31	26	
			SAE EMI Level	4	3.5	-

^{1.} Data based on characterization results, not tested in production.

4.7.3 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU and DLU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). The Human Body Model is simulated. This test conforms to the JESD22-A114A standard.

Table 19. Absolute maximum ratings

Symbol	Ratings	Conditions	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (Human body model)	T _A =+25 °C	2000	V

^{1.} Data based on characterization results, not tested in production.

Static and dynamic latch-up

- LU: 3 complementary static tests are required on 10 parts to assess the latch-up performance. A supply overvoltage (applied to each power supply pin) and a current injection (applied to each input, output and configurable I/O pin) are performed on each sample. This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.
- DLU: Electrostatic discharges (one positive then one negative test) are applied to each
 pin of 3 samples when the micro is running to assess the latch-up performance in
 dynamic mode. Power supplies are set to the typical values, the oscillator is connected

as near as possible to the pins of the micro and the component is put in reset mode. This test conforms to the IEC1000-4-2 and SAEJ1752/3 standards. For more details, refer to the application note AN1181.

Table 20. Electrical sensitivities

Symbol	Parameter	Conditions	Class ⁽¹⁾	
LU	Static latch-up class	T _A =+25°C	A	
DLU	Dynamic latch-up class	V_{DD} =5.5V, f_{OSC} =4MHz, T_A =+25°C	А	

Class description: A Class is an STMicroelectronics internal specification. All its limits are higher than the JEDEC specifications, that means when a device belongs to Class A it exceeds the JEDEC standard. B Class strictly covers all the JEDEC criteria (international standard).

4.8 Communication interface characteristics

Table 21. USB DC electrical characteristics

Parameter	Symbol	Conditions	Min.	Max.	Unit
Input levels					
Differential input sensitivity	VDI	I(D+, D-)	0.2		V
Differential common mode range	VCM	Includes VDI range	0.8	2.5	V
Single ended receiver threshold	VSE		1.3	2.0	V
Output levels					
Static output low	VOL	RL of 1.5 k Ω to 3.6 V ⁽¹⁾		0.3	V
Static output high	VOH	RL of 15 k Ω to V _{SS} ⁽¹⁾	2.8	3.6	V
USBVCC: voltage level	USBV	V _{DD} =5 V	3.00	3.60	V

^{1.} R_L is the load connected on the USB drivers. All the voltages are measured from the local ground potential.

Figure 6. USB data signal rise and fall time

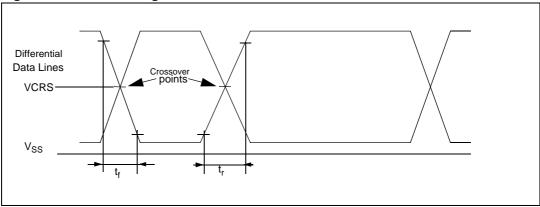


Table 22. USB full-speed electrical characteristics

Parameter	Symbol	Conditions	Min	Max	Unit
Driver characteristics					
Rise time ⁽¹⁾	t _r	CL=50 pF	4	20	ns
Fall Time ⁽¹⁾	t _f	CL=50 pF	4	20	ns
Rise/ Fall time matching	t _{rfm}	t _r /t _f	90	110	%
Output signal crossover voltage	VCRS		1.3	2.0	V

Measured from 10% to 90% of the data signal. For more detailed informations, please refer to Chapter 7 (Electrical) of the USB specification (version 1.1).

5 Package characteristics

In order to meet environmental requirements, ST offers these devices in ECOPACK® package. The package has a lead-free second level interconnect. The category of second Level Interconnect is marked on the package and on the inner box label, in compliance with JEDEC standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label.

ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

5.1 Package mechanical data

Figure 7. 24-lead very thin fine pitch quad flat no-lead 5x5 mm 0.65 mm pitch, package outline

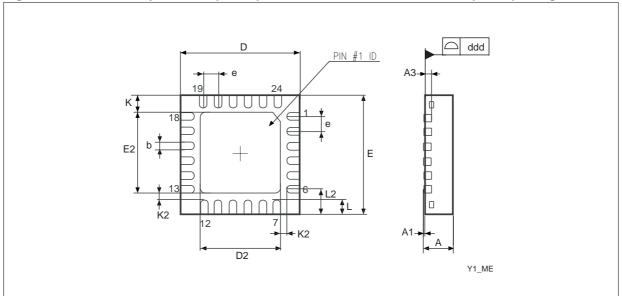


Table 23. 24-lead very thin fine pitch quad flat no-lead 5x5mm,0.65mm pitch, mechanical data

Dim.	mm			inches ⁽¹⁾		
Dilli.	Min	Тур	Max	Min	Тур	Max
А	0.800	0.900	1.000	0.0315	0.0354	0.0394
A1	0.000	0.020	0.050	0.0000	0.0010	0.0020
A3		0.020			0.0008	
b	0.250	0.300	0.350	0.0098	0.0118	0.0138
D		5.000			0.1969	
D2	3.500	3.600	3.700	0.1378	0.1417	0.1457
E		5.000			0.1969	
D2	3.500	3.600	3.700	0.1378	0.1417	0.1457
е		0.650			0.0256	
L	0.350	0.450	0.550	0.0138	0.0177	0.0217
L2	0.870	0.875	0.880	0.0343	0.0344	0.0346
ddd	0.080			0.0031		

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.

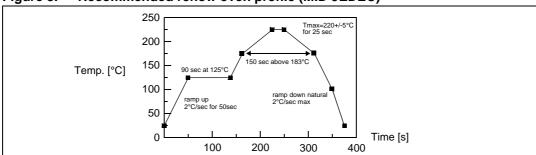


Figure 8. Recommended reflow oven profile (MID JEDEC)

6 Device configuration and ordering information

Device ordering information and transfer of customer code

Customer code is made up of the ROM contents and the list of the selected options (if any). The ROM contents are to be sent on diskette, or by electronic means, with the hexadecimal file in .S19 format generated by the development tool. All unused bytes must be set to FFh.

The selected options are communicated to STMicroelectronics using the correctly completed OPTION LIST appended. See *Figure 9: ST7LCR option list*.

Refer to application note AN1635 for information on the counter listing returned by ST after code has been transferred.

The STMicroelectronics Sales Organization will be pleased to provide detailed information on contractual points.

Table 24. Ordering information

Sales type	Program memory (bytes)	RAM (bytes)	Package
ST7LCRE4U1/xxx ⁽¹⁾	16K ROM	768	VFQFPN24
ST7LCRDIE6/xxx ⁽¹⁾	16K ROM	768	Die

^{1.} Customer ROM code name is assigned by STMicroelectronics.

Figure 9. ST7LCR option list

	(Last u	pdate: October 2007)
Address:		
Contact:		
Reference/ROM Code*: *The ROM code name is ROM code must be sent		STMicroelectronics. matHex extension cannot be processed.
Device Type/Memory Siz	e/Package (d	check only one option)
ROM Device:	16K	
VFQFPN24: DIE24:		
Conditioning (check or		
Packaged Product:	1	Die Product
[] Tray (VFQFPN packa	ge only) 	
Special Marking: [] Authorized characters	No [] are letters,	Yes " " digits, '.', '-', '/' and spaces only.
Maximum character cour	t: VFQFPN24	(7 char. max) :
Vcc Card:	CRDVCC	[] 1.8V [] 3.0V
Watchdog:	WDGSW	[] Software Activation [] Hardware Activation
Nested Interrupts NEST	1	[] Nested Interrupts [] Non Nested Interrupts
ISO Clock Source ISO	LK	[] Oscillator [] Divider
No. of Retries	RETRY	
Readout Protection:	FMP_R	[] Disabled [] Enabled
		Signature

7 Revision history

28/29

Table 25. Document revision history

Date	Revision	Changes
26-Aug-06	0.1	Initial release
26-Mar-07	0.2	QFN24 package added Option List added External clock source frequency modified (to maximum value), Section 4.2 Die sales type added to Table Note added to Table 2 (NC pins must be connected to ground)
23-Oct-2007	1	Document reformatted. Replaced ST7LCR by ST7LCRE4U1and ST7LCRDIE6. ECOPACK text added. Changed "selectable card V _{CC} " into "fixed card V _{CC} ". 5 V removed in Section: Features, Section 3: ST7LCR implementation and Table 16: Smartcard supply supervisor electrical characteristics. Changed QFN24 into VFQFPN24. Added Figure 8: Recommended reflow oven profile (MID JEDEC). CRDC4 and CRDC8 renamed C4 and C8 respectively in Figure 1: ST7LCR block diagram. Removed LED functional block and LEDO pin from Figure 1: ST7LCR block diagram. LEDO pin left unconnected in Figure 2: 24-lead VFQFPN package pinout and Table 2: Pin description, and Figure 3: Smartcard interface reference application - VFQFPN24 pin block diagram. Removed mention of external LEDS in Section 3.1: Functionality. SLEF and DIODE pins removed from Figure 1: ST7LCR block diagram, and left unconnected in Figure 2: 24-lead VFQFPN package pinout, Table 2: Pin description, and Figure 3: Smartcard interface reference application - VFQFPN24 pin block diagram. Removed LED pin characteristics table. Added Figure 8: Recommended reflow oven profile (MID JEDEC). Updated Figure 9: ST7LCR option list.

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